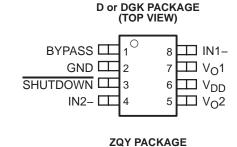
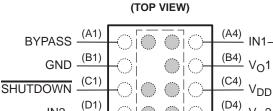
TPA6101A2 50-mW ULTRALOW-VOLTAGE, FIXED-GAIN STEREO HEADPHONE AUDIO POWER AMPLIF

SLOS331C - AUGUST 2000 - REVISED MARCH 2007

GND

- Minimal External Components Required
- 1.6-V to 3.6-V Supply Voltage Range
- 50-mW Stereo Output
- Low Supply Current . . . 0.75 mA
- Low Shutdown Current . . . 50 nA
- Gain Set Internally to 2 dB
- **Pop Reduction Circuitry**
- **Internal Mid-Rail Generation**
- Thermal and Short-Circuit Protection
- **Surface-Mount Packaging**
 - 3-mm × 5-mm MSOP Package (DGN)
 - 5-mm × 6-mm SOIC Package (D)
 - 2,5-mm × 2,5-mm MicroStar Junior™ BGA Package (ZQY)





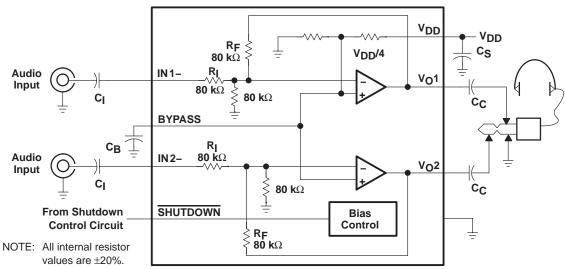
description

The TPA6101A2 is a stereo audio power amplifier packaged in an 8-pin SOIC package, an 8-pin MSOP package, or a 15-ball BGA package, capable of delivering 50 mW of continuous RMS power per channel into 16- Ω loads. Amplifier gain is internally set to 2 dB (inverting) to save board space by eliminating six external resistors.

The TPA6101A2 is optimized for battery applications because of its low supply current, shutdown current, and THD+N. To obtain the low-supply-voltage range, the TPA6101A2 biases BYPASS to $V_{DD}/4$.

When driving a 16- Ω load with 40-mW output power from 3.3 V, THD+N is 0.08% at 1 kHz, and less than 0.2% across the audio band of 20 Hz to 20 kHz. For 30 mW into 32-Ω loads, the THD+N is reduced to less than 0.06% at 1 kHz, and is less than 0.3% across the audio band of 20 Hz to 20 kHz.

typical application circuit





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

MicroStar BGA is a trademark of Texas Instruments.



TPA6101A2 50-mW ULTRALOW-VOLTAGE, FIXED-GAIN STEREO HEADPHONE AUDIO POWER AMPLIFIER

AVAILABLE OPTIONS

ı	Τ.	F	PACKAGED DEVICE MSOP BO			BGA
ı	IA.	SMALL OUTLINE (D)	MSOP (DGK)	BGA (ZQY)	SYMBOLIZATION	SYMBOLIZATION
ı	-40°C to 85°C	TPA6101A2D	TPA6101A2DGK	TPA6101A2ZQYR	AJM	AAQI

Terminal Functions

TERM	INAL				
	N(NO.		DESCRIPTION	
NAME	D, DGK ZQY		1/0	= ====================================	
BYPASS	1	A1	I	Tap to voltage divider for internal mid-supply bias supply. BYPASS is set at $V_{DD}/4$. Connect to a 0.1- μ F to 1- μ F low-ESR capacitor for best performance.	
GND	2	B1	-	GND is the ground connection.	
IN1-	8	A4	Ι	IN1- is the inverting input for channel 1.	
IN2-	4	D1	_	IN2- is the inverting input for channel 2.	
SHUTDOWN	3	C1	_	Active-low input. When held low, the device is placed in a low-supply-current mode.	
V_{DD}	6	C4	ı	V _{DD} is the supply voltage terminal.	
V _O 1	7	В4	0	V _O 1 is the audio output for channel 1.	
V _O 2	5	D4	0	V _O 2 is the audio output for channel 2.	

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V _{DD}	4 V
Input voltage, V _I	\dots -0.3 V to V _{DD} + 0.3 V
Continuous total power dissipation	Internally Limited
Operating junction temperature range, T _J	–40°C to 150°C
Storage temperature range, T _{stq}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D	710 mW	5.68 mW/°C	454 mW	369 mW
DGK	469 mW	3.75 mW/°C	300 mW	244 mW
ZQY	2 W	17.1 mW/°C	1.28 W	1.04 W

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V _{DD}	1.6	3.6	V
High-level input voltage, V _{IH} (SHUTDOWN)	0.6 V _{DD}		V
Low-level input voltage, V _{IL} (SHUTDOWN)		0.25 V _{DD}	V
Operating free-air temperature, T _A	-40	85	°C



TPA6101A2 50-mW ULTRALOW-VOLTAGE, FIXED-GAIN STEREO HEADPHONE AUDIO POWER AMPLIFIER

dc electrical characteristics at T_A = 25°C, V_{DD} = 3.6 V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Voo	Output offset voltage	$A_V = 2 dB$		5	40	mV
PSRR	Power supply rejection ratio	V _{DD} = 3 V to 3.6 V		72		dB
I _{DD}	Supply current	SHUTDOWN = 3.6 V		0.75	1.5	mA
I _{DD(SD)}	Supply current in SHUTDOWN mode	SHUTDOWN = 0 V		50	250	nA
I _{IH}	High-level input current (SHUTDOWN)	$V_{DD} = 3.6 \text{ V}, V_I = V_{DD}$			1	μΑ
I _{IL}	Low-level input current (SHUTDOWN)	$V_{DD} = 3.6 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
Z _I	Input impedance			80		kΩ

ac operating characteristics, $\rm V_{DD}$ = 3.3 V, $\rm T_A$ = 25°C, $\rm R_L$ = 16 Ω

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
G	Gain			2		dB
PO	Output power (each channel)	THD ≤ 0.1%, f = 1 kHz		50		mW
THD+N	Total harmonic distortion + noise	$P_0 = 45 \text{ mW}, 20 \text{ Hz} - 20 \text{ kHz}$		0.4%		
Вом	Maximum output power BW	THD < 0.5%		> 20		kHz
k _{SVR}	Supply ripple rejection ratio	f = 1 kHz		47		dB
SNR	Signal-to-noise ratio	P _O = 50 mW		86		dB
Vn	Noise output voltage (no-noise weighting filter)			45		μV(rms)

ac operating characteristics, $\rm V_{DD}$ = 3.3 V, $\rm T_A$ = 25°C, $\rm R_L$ = 32 $\rm \Omega$

	PARAMETER	TEST CONDITIONS	MIN TY	'P MAX	UNIT
G	Gain			2	dB
PO	Output power (each channel)	THD \leq 0.1%, f = 1 kHz	;	35	mW
THD+N	Total harmonic distortion + noise	$P_0 = 30 \text{ mW}, 20 \text{ Hz}-20 \text{ kH}$	lz 0.4	%	
Вом	Maximum output power BW	THD < 0.4%	>	20	kHz
ksvr	Supply ripple rejection ratio	f = 1 kHz	4	47	dB
SNR	Signal-to-noise ratio	P _O = 30 mW	3	36	dB
Vn	Noise output voltage (no-noise weighting filter)			50	μV(rms)

TPA6101A2 50-mW ULTRALOW-VOLTAGE, FIXED-GAIN STEREO HEADPHONE AUDIO POWER AMPLIFIER

dc electrical characteristics at $T_A = 25$ °C, $V_{DD} = 1.6$ V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V ₀₀	Output offset voltage	$A_V = 2 dB$		5	40	mV
PSRR	Power supply rejection ratio	V _{DD} = 1.4 V to 1.8 V		80		dB
IDD	Supply current	SHUTDOWN = 1.6 V		0.65	1.2	mA
I _{DD(SD)}	Supply current in SHUTDOWN mode	SHUTDOWN = 0 V		50	250	nA
IIIII	High-level input current (SHUTDOWN)	$V_{DD} = 1.6 \text{ V}, V_I = V_{DD}$			1	μΑ
I _I L	Low-level input current (SHUTDOWN)	$V_{DD} = 1.6 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
Z _l	Input impedance		·	80		kΩ

ac operating characteristics, V_{DD} = 1.6 V, T_A = 25°C, R_L = 16 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		2	dB
PO	Output power (each channel)	THD \leq 0.5%, f = 1 kHz	10	mW
THD+N	Total harmonic distortion + noise	$P_0 = 9.5 \text{ mW}, 20 \text{ Hz} - 20 \text{ kHz}$	0.06%	
ВОМ	Maximum output power BW	THD < 1%	> 20	kHz
ksvr	Supply ripple rejection ratio	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	P _O = 10 mW	82	dB
V _n	Noise output voltage (no-noise weighting filter)		32	μV(rms)

ac operating characteristics, V_{DD} = 1.6 V, T_{A} = 25°C, R_{L} = 32 Ω

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
G	Gain		2	dB
PO	Output power (each channel)	THD \leq 0.5%, f = 1 kHz	7.5	mW
THD+N	Total harmonic distortion + noise	$P_{O} = 6.5 \text{ mW}, 20 \text{ Hz}-20 \text{ kHz}$	0.05%	
ВОМ	Maximum output power BW	THD < 1%	>20	kHz
ksvr	Supply ripple rejection ratio	f = 1 kHz	47	dB
SNR	Signal-to-noise ratio	$P_{O} = 7.5 \text{ mW}$	84	dB
V _n	Noise output voltage (no-noise weighting filter)		32	μV(rms)

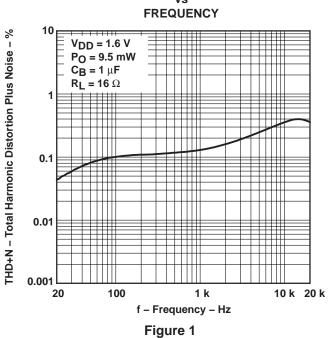
TYPICAL CHARACTERISTICS

Table of Graphs

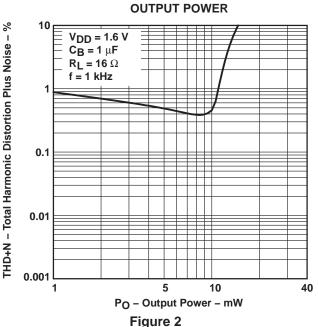
			FIGURE
		vs Frequency	1, 3, 5, 7, 9, 11
THD+N	Total harmonic distortion plus noise	vs Output power	2, 4, 6, 8, 10, 12
		vs Output voltage	13, 14
PO	Output power	vs Load resistance	15, 16
ksvr	Supply ripple rejection ratio	vs Frequency	17, 18
Vn	Output noise voltage	vs Frequency	19, 20
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	Closed-loop gain and phase	vs Frequency	23, 24, 25, 26
I _{DD}	Supply current	vs Supply voltage	27
PD	Power dissipation	vs Output power	28



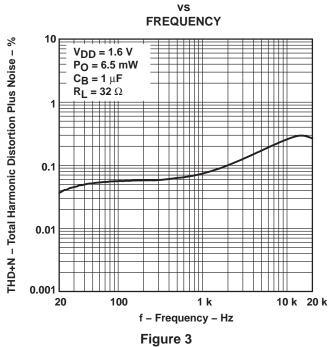
TOTAL HARMONIC DISTORTION PLUS NOISE



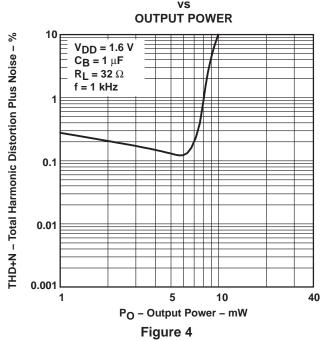
TOTAL HARMONIC DISTORTION PLUS NOISE vs



TOTAL HARMONIC DISTORTION PLUS NOISE

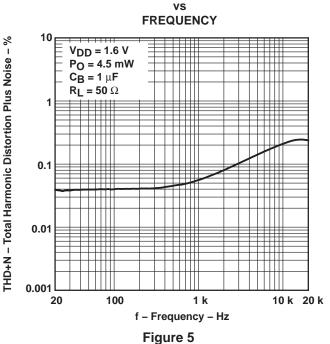


TOTAL HARMONIC DISTORTION PLUS NOISE

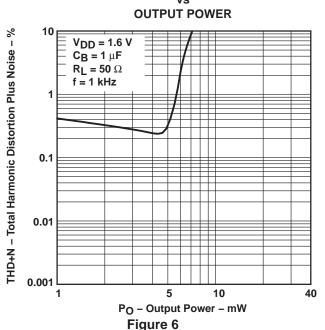




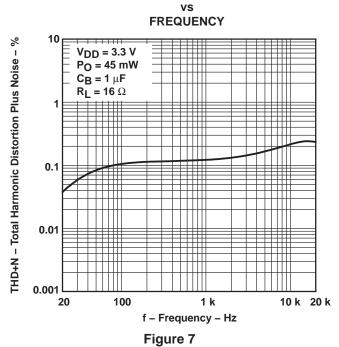
TOTAL HARMONIC DISTORTION PLUS NOISE



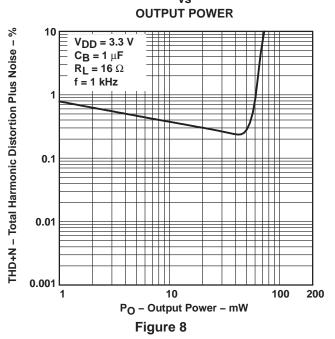
TOTAL HARMONIC DISTORTION PLUS NOISE



TOTAL HARMONIC DISTORTION PLUS NOISE

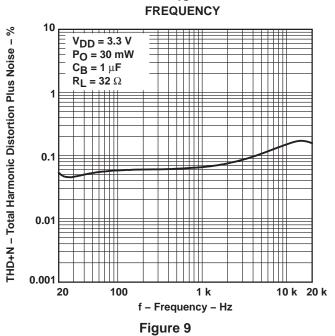


TOTAL HARMONIC DISTORTION PLUS NOISE





TOTAL HARMONIC DISTORTION PLUS NOISE vs FREQUENCY



TOTAL HARMONIC DISTORTION PLUS NOISE vs

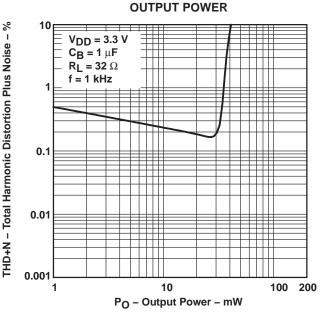
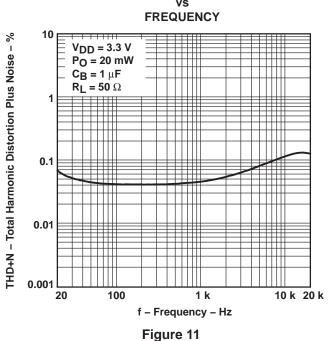
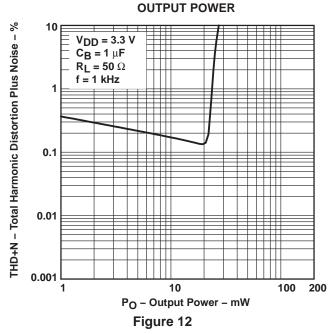


Figure 10

TOTAL HARMONIC DISTORTION PLUS NOISE



TOTAL HARMONIC DISTORTION PLUS NOISE vs



TOTAL HARMONIC DISTORTION PLUS NOISE vs

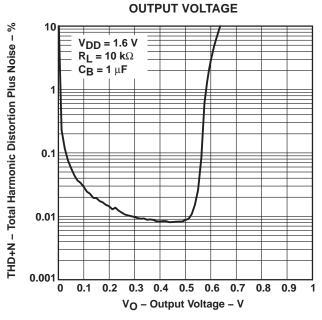
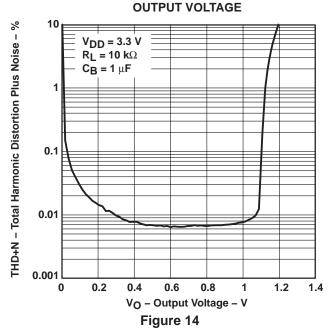


Figure 13

TOTAL HARMONIC DISTORTION PLUS NOISE vs





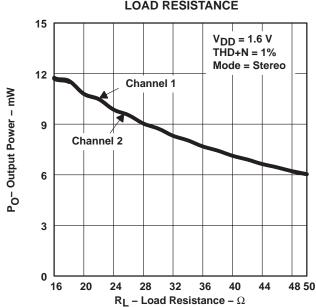
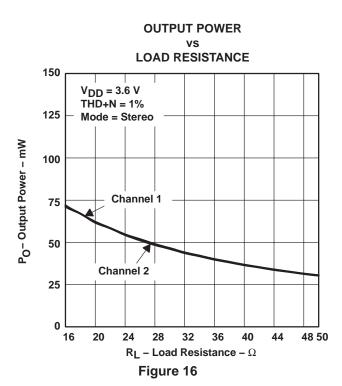


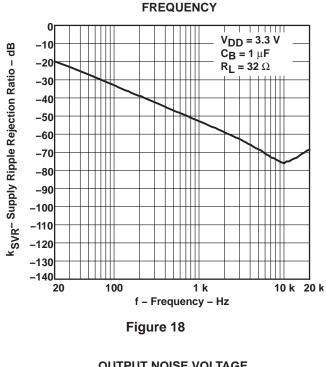
Figure 15



TEXAS INSTRUMENTS

SUPPLY RIPPLE REJECTION RATIO FREQUENCY 0 $V_{DD} = 1.6 V$ -10 k_{SVR}- Supply Ripple Rejection Ratio - dB $C_B = 1 \mu F$ -20 $R_L = 32 \Omega$ -30 -40 -50 -60 -70 -80 -90 -100 -110 -120 -130-140 20 100 1 k 10 k 20 k f - Frequency - Hz





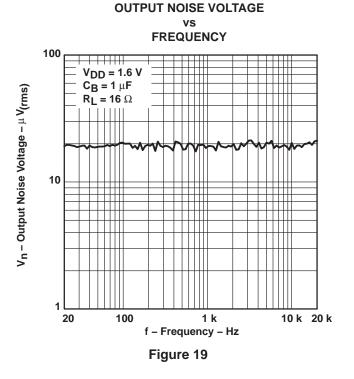
SUPPLY RIPPLE REJECTION RATIO

vs

OUTPUT NOISE VOLTAGE

vs

FREQUENCY



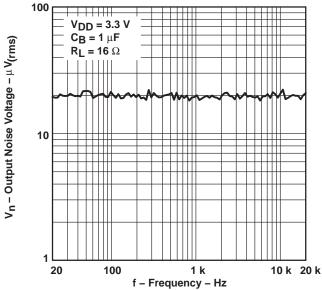
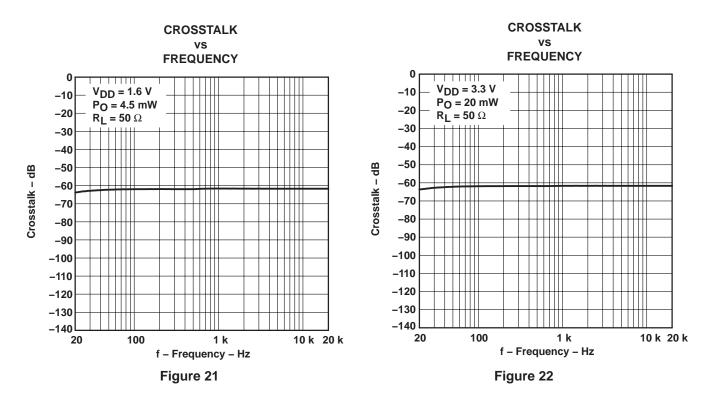
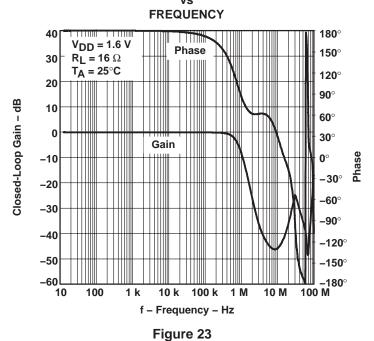


Figure 20



CLOSED-LOOP GAIN AND PHASE vs



CLOSED-LOOP GAIN AND PHASE

FREQUENCY

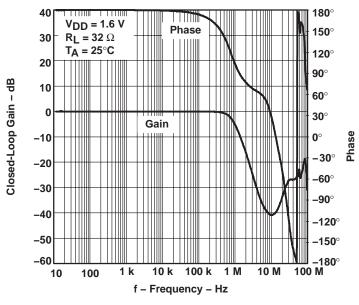


Figure 24

CLOSED-LOOP GAIN AND PHASE

vs FREQUENCY

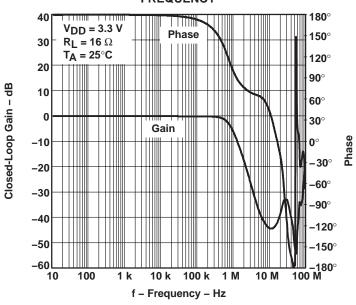


Figure 25



CLOSED-LOOP GAIN AND PHASE vs

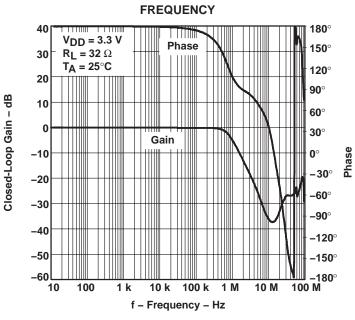
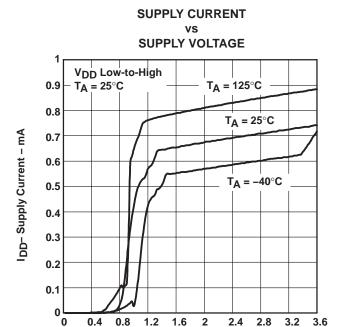
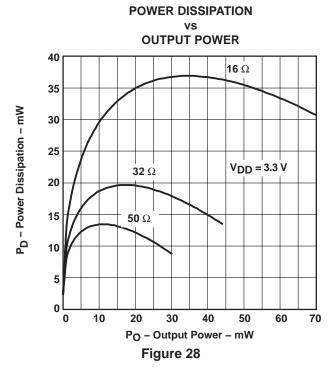


Figure 26



V_{DD} – Supply Voltage – V Figure 27





APPLICATION INFORMATION

input capacitor, CI

In the typical application, an input capacitor (C_I) is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case, C_I and R_I form a high-pass filter with the corner frequency determined in equation 1. R_I is set internally and is fixed at 80 k Ω .

$$f_{C} = \frac{1}{2\pi R_{I}C_{I}} \tag{1}$$

The value of C_l is important to consider, as it directly affects the bass (low-frequency) performance of the circuit. Consider the example where the specification calls for a flat bass response down to 20 Hz. Equation 1 is reconfigured as equation 2.

$$C_{l} = \frac{1}{2\pi R_{l} f_{c}}$$
 (2)

In this example, C_I is approximately 0.1 μ F. A further consideration for this capacitor is the leakage path from the input source through the input network (R_I , C_I) and the feedback resistor (R_F) to the load. This leakage current creates a dc-offset voltage at the input to the amplifier that reduces useful headroom. For this reason, a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications, as the dc level there is held at $V_{DD}/4$, which is likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

power supply decoupling, CS

The TPA6101A2 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 μ F, placed as close as possible to the device V_{DD} lead, works best. For filtering lower-frequency noise signals, a larger, aluminum electrolytic capacitor of 10 μ F or greater placed near the power amplifier is recommended.

midrail bypass capacitor, C_B

The midrail bypass capacitor (C_B) serves several important functions. During start-up, C_B determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a $55-k\Omega$ source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in Euation 3 should be maintained.

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}} \times 55 \,\mathsf{k}\Omega\right)} \le \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \tag{3}$$

As an example, consider a circuit where C_B is 1 μ F, C_I is 0.1 μ F, and R_I is 80 $k\Omega$. Inserting these values into Euation 3 results in: 18.18 \leq 125 which satisfies the rule. Bypass capacitor (C_B) values of 0.47 μ F to 1 μ F and ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

APPLICATION INFORMATION

output coupling capacitor, CC

In the typical single-supply, single-ended (SE) configuration, an output coupling capacitor (C_C) is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load from a high-pass filter is governed by Equation 4.

$$f_{C} = \frac{1}{2\pi R_{I} C_{C}} \tag{4}$$

The main disadvantage, from a performance standpoint, is that the typically small load impedances drive the low-frequency corner higher. Large values of C_C are required to pass low-frequencies into the load. Consider the example where a C_C of 68 μF is chosen and loads vary from 32 Ω to 47 $k\Omega$. Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances vs Low-Frequency Output Characteristics in SE Mode

RL	СС	LOWEST FREQUENCY
32 Ω	68 μF	73 Hz
10,000 Ω	68 μF	0.23 Hz
47,000 Ω	68 μF	0.05 Hz

As Table 1 indicates, headphone response is adequate and drive into line-level inputs (a home stereo for example) is very good.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:

$$\frac{1}{\left(C_{\mathsf{B}} \times 55 \,\mathsf{k}\Omega\right)} \le \frac{1}{\left(C_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \ll \frac{1}{\mathsf{R}_{\mathsf{L}}\mathsf{C}_{\mathsf{C}}} \tag{5}$$

using low-ESR capacitors

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

3.3-V versus 1.6-V operation

The TPA6101A2 was designed for operation over a supply range of 1.6 V to 3.6 V. There are no special considerations for 1.6-V versus 3.3-V operation as far as supply bypassing, gain setting, or stability. Supply current is slightly reduced from 0.75 mA (typical) to 0.65 mA (typical). The most important consideration is that of output power. Each amplifier can produce a maxium output voltage swing within a few hundred millivolts of the rails with a 10-k Ω load. However, this voltage swing decreases as the load resistance decreases, and the rDS(on) of the output stage transistors becomes more significant. For example, for a 32- Ω load, the maximum peak output voltage with VDD = 1.6 V is approximately 0.7 V with no clipping distortion. This reduced voltage swing effectively reduces the maximum undistorted output power.







.com 6-Dec-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TPA6101A2D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA6101A2DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA6101A2DGKR	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPA6101A2DGKRG4	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

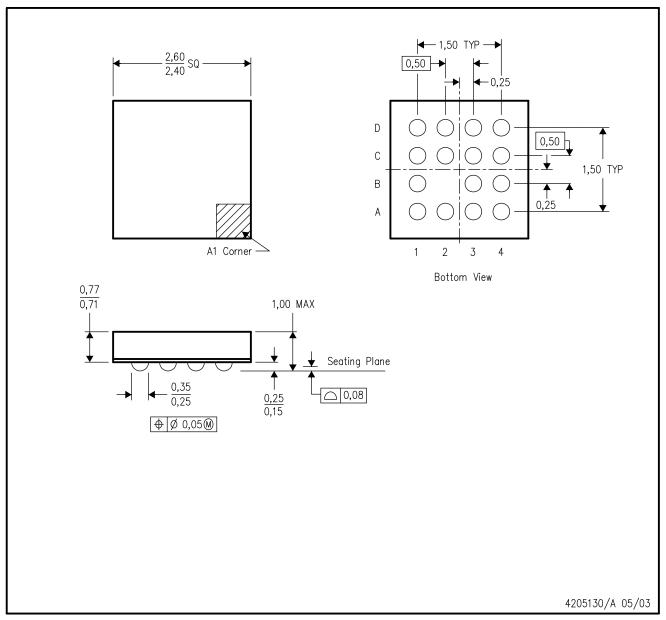
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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ZQY (S-PBGA-N15)

PLASTIC BALL GRID ARRAY



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. MicroStar Junior configuration
- D. Falls within JEDEC MO-225
- E. This package is lead-free.



DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



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